

- GENERAL PURPOSE SILICON DIODES
- ALL JUNCTIONS COMPLETELY PROTECTED WITH SILICON DIOXIDE
- COMPATIBLE WITH ALL WIRE BONDING AND DIE ATTACH TECHNIQUES EXCEPT SOLDER REFLOW

CD483B  
 CD485B  
 CD486B  
 CD645  
 AND  
 CD5194 thru CD5196

### MAXIMUM RATINGS

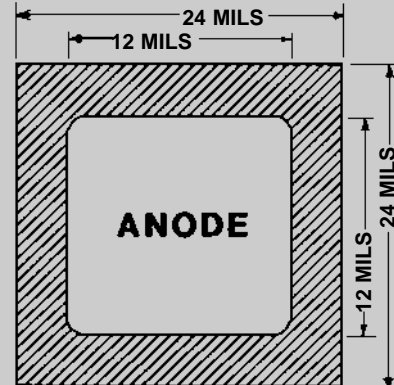
Operating Temperature: -65°C to +175°C  
 Storage Temperature: -65°C to +175°C

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V <sub>RM</sub>	V <sub>RWM</sub>	I <sub>O</sub>	I <sub>O</sub> T <sub>A</sub> =+150°C	I <sub>FSM</sub> t <sub>p</sub> = 1/120 S T <sub>A</sub> =25°C
	V(pk)	V(pk)	mA	mA	A
CD483B	80	70	200	50	2
CD485B	180	180	200	50	2
CD486B	250	225	200	50	2
CD645	270	225	400	150	5
CD5194	80	70	200	50	2
CD5195	180	180	200	50	2
CD5196	250	225	200	50	2

TYPE	V <sub>F</sub> (1)	I <sub>R1</sub> at V <sub>RWM</sub> T <sub>A</sub> +25°C	I <sub>R2</sub> at V <sub>RM</sub> T <sub>A</sub> +25°C	I <sub>R3</sub> at V <sub>RWM</sub> T <sub>A</sub> +150°C	CAP @V <sub>R</sub> =4V
	V dc	nA dc	μA	μA dc	pF
CD483B	0.8 - 1.0	25	100	5	-
CD485B	0.8 - 1.0	25	100	5	-
CD486B	0.8 - 1.0	25	100	5	-
CD645	0.8 - 1.0	50	50	25	2.0
CD5194	0.8 - 1.0	25	100	5	-
CD5195	0.8 - 1.0	25	100	5	-
CD5196	0.8 - 1.0	25	100	5	-

NOTE 1 AT 100mA (pulsed) except for CD645 which is at 400mA (pulsed)



### DESIGN DATA

#### METALLIZATION:

Top: (Anode).....Al  
 Back: (Cathode).....Au

AL THICKNESS .....25,000 Å Min

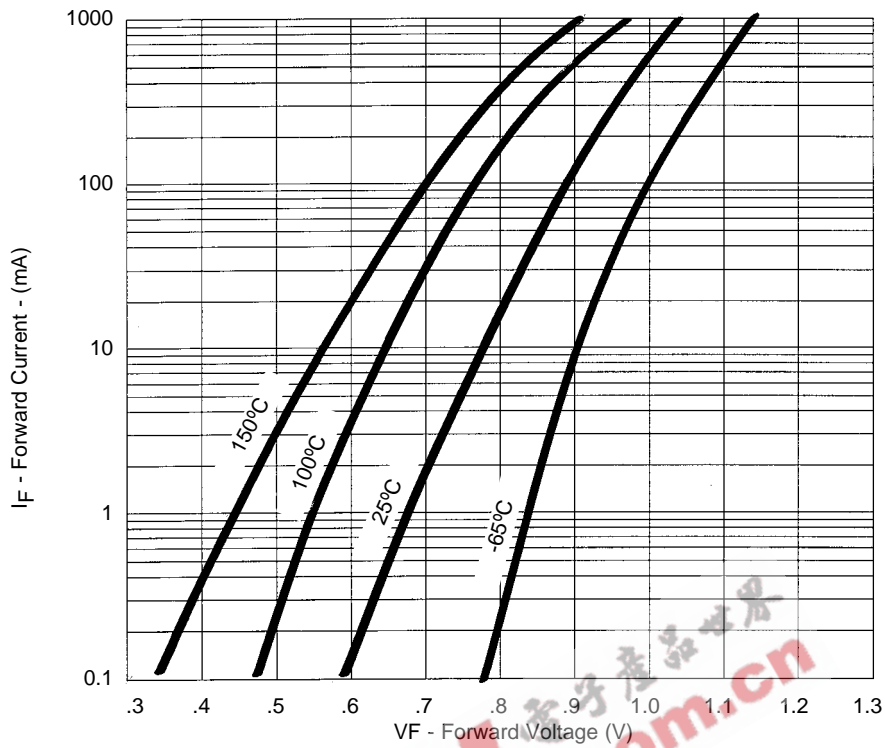
GOLD THICKNESS .....4,000 Å Min

CHIP THICKNESS .....10 Mils

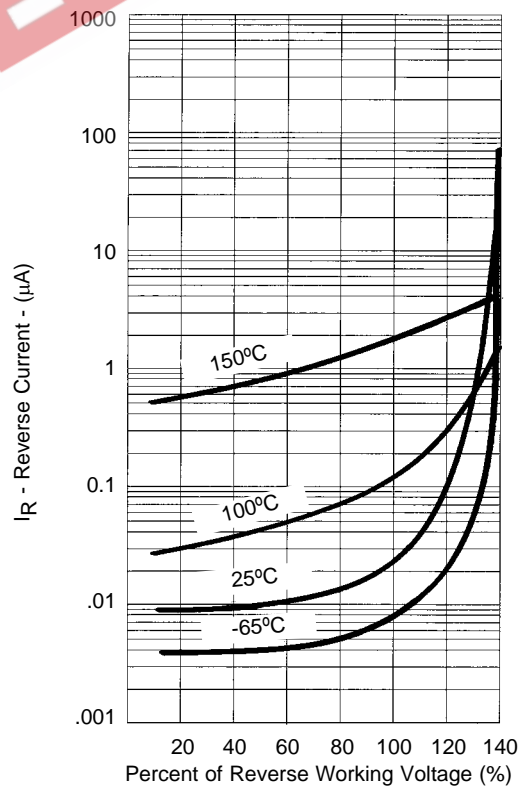
TOLERANCES: ALL  
 Dimensions ± 2 mils



# CD483B, CD485B, CD486B, CD645, CD5194 thru CD5196



**FIGURE 2**  
Typical Forward Current  
vs Forward Voltage



**NOTE :** All temperatures shown on graphs are junction temperatures

**FIGURE 3**  
Typical Reverse Current  
vs Reverse Voltage